

**Refine Search**

10/630,969

**Search Results -**

Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1

**Database:**

- US Pre-Grant Publication Full-Text Database
- US Patents Full-Text Database
- US OCR Full-Text Database
- EPO Abstracts Database
- JPO Abstracts Database
- Derwent World Patents Index
- IBM Technical Disclosure Bulletins

**Search:**

Refine Search

Recall Text
Clear
Interrupt

**Search History**

**DATE:** Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

<u>Set</u>	<u>Hit Count</u>	<u>Set</u>
<u>Name</u>	<u>Query</u>	<u>Name</u>
side by side		
DB=USPT; PLUR=YES; OP=ADJ		
<u>L6</u>	L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1 L6
<u>L5</u>	L3 and oxidation	20 L5
<u>L4</u>	L3 and oxidation and (sio2)	0 L4
<u>L3</u>	L2 and (inert or argon or ar or helium or he or neon or ne or kr or krypton or xenon or nitrogen)	45 L3
<u>L2</u>	L1 and ((ratio) near3 (nitrogen and oxygen))	45 L2
<u>L1</u>	microstructure	23090 L1

END OF SEARCH HISTORY

## Hit List

---

Search Results - Record(s) 1 through 1 of 1 returned.

---

- 1. Document ID: US 6071601 A

L6: Entry 1 of 1

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

---

Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio)	1

---

Display Format:

[Previous Page](#)    [Next Page](#)    [Go to Doc#](#)

## Refine Search

---

### Search Results -

Terms	Documents
L5 and pressure and torr	5

---

**Database:**

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

---

**Search:**

L7

Recall Text

Clear

Interrupt

---

### Search History

---

**DATE:** Tuesday, June 29, 2004    [Printable Copy](#)    [Create Case](#)

<u>Set</u>	<u>Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
	side by side			result set
DB=USPT; PLUR=YES; OP=ADJ				
L7	L5 and pressure and torr		5	L7
L6	L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)		1	L6
L5	L3 and oxidation		20	L5
L4	L3 and oxidation and (sio2)		0	L4
L3	L2 and (inert or argon or ar or helium or he or neon or ne or kr or krypton or xenon or nitrogen)		45	L3
L2	L1 and ((ratio) near3 (nitrogen and oxygen))		45	L2
L1	microstructure		23090	L1

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

### Search Results - Record(s) 1 through 5 of 5 returned.

#### □ 1. Document ID: US 6498097 B1

L7: Entry 1 of 5

File: USPT

Dec 24, 2002

US-PAT-NO: 6498097

DOCUMENT-IDENTIFIER: US 6498097 B1

TITLE: Apparatus and method of forming preferred orientation-controlled platinum film using oxygen

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

#### □ 2. Document ID: US 6071601 A

L7: Entry 2 of 5

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

#### □ 3. Document ID: US 6054331 A

L7: Entry 3 of 5

File: USPT

Apr 25, 2000

US-PAT-NO: 6054331

DOCUMENT-IDENTIFIER: US 6054331 A

TITLE: Apparatus and methods of depositing a platinum film with anti-oxidizing function over a substrate

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

#### □ 4. Document ID: US 5143879 A

L7: Entry 4 of 5

File: USPT

Sep 1, 1992

US-PAT-NO: 5143879

DOCUMENT-IDENTIFIER: US 5143879 A  
\*\* See image for Certificate of Correction \*\*

TITLE: Method to recover organic templates from freshly synthesized molecular sieves

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Abstract](#) | [Claims](#) | [KMC](#) | [Drawn Obj](#)

---

5. Document ID: US 4762728 A

L7: Entry 5 of 5

File: USPT

Aug 9, 1988

US-PAT-NO: 4762728

DOCUMENT-IDENTIFIER: US 4762728 A

TITLE: Low temperature plasma nitridation process and applications of nitride films formed thereby

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Abstract](#) | [Claims](#) | [KMC](#) | [Drawn Obj](#)

---

[Clear](#) | [Generate Collection](#) | [Print](#) | [Fwd Refs](#) | [Bkwd Refs](#) | [Generate OACS](#)

Terms	Documents
L5 and pressure and torr	5

---

Display Format:  [Change Format](#)

[Previous Page](#)    [Next Page](#)    [Go to Doc#](#)

**Hit List***10/6/30, 969*

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

**Search Results - Record(s) 1 through 4 of 4 returned.** **1. Document ID: US 6548343 B1**

L24: Entry 1 of 4

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMNC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

 **2. Document ID: US 6485988 B2**

L24: Entry 2 of 4

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMNC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

 **3. Document ID: US 6413386 B1**

L24: Entry 3 of 4

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMNC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

 **4. Document ID: US 6362093 B1**

L24: Entry 4 of 4

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

[Full] [Title] [Citation] [Front] [Review] [Classification] [Date] [Reference] [Claims] [KWM] [Drawn D]

[Clear]

[Generate Collection]

[Print]

[Fwd Refs]

[Bkwd Refs]

[Generate QACs]

Terms	Documents
L23 and (silicon adj oxynitride)	4

Display Format: [Tl] [Change Format]

[Previous Page]

[Next Page]

[Go to Doc#]

## Refine Search

---

### Search Results -

Terms	Documents
L23 and (silicon adj oxynitride)	4

---

**Database:**

[US Pre-Grant Publication Full-Text Database](#)  
[US Patents Full-Text Database](#)  
[US OCR Full-Text Database](#)  
[EPO Abstracts Database](#)  
[JPO Abstracts Database](#)  
[Derwent World Patents Index](#)  
[IBM Technical Disclosure Bulletins](#)

**Search:**

Refine Search

Recall Text
Clear
Interrupt

---

### Search History

---

DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

<u>Set</u> <u>Name</u> <u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
side by side		
<i>DB=USPT; PLUR=YES; OP=ADJ</i>		
<u>L24</u> L23 and (silicon adj oxynitride)	4	<u>L24</u>
<u>L23</u> L22 and (silicon adj oxide)	7	<u>L23</u>
<u>L22</u> L21 and oxide and (oxygen adj containing)	11	<u>L22</u>
<u>L21</u> L20 and semiconductor and (flow adj rate)	80	<u>L21</u>
<u>L20</u> L19 and (inert or h2 or ne or ar or xe or neon or argon or krypton or kr) (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1159	<u>L20</u>
<u>L19</u> L18 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	2645	<u>L19</u>
<u>L18</u> L17 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L18</u>
<u>L17</u> L16 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L17</u>
<u>L16</u> L15 and (inert or argon or neon or hydrogen or xenon or krypton)	0	<u>L16</u>
<u>L15</u> L14 and (inert or argon or neon or hydrogen or xenon or krypton) and (high adj K)	56	<u>L15</u>
<u>L14</u> L13 near10 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L14</u>
<u>L13</u>	0	<u>L13</u>

<u>L12</u>	L11 near5 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L12</u>
<u>L11</u>	(flow adj rate) near4 (3:1)	76	<u>L11</u>
<u>L10</u>	l2 and (3:1)	8	<u>L10</u>
<u>L9</u>	l2 and (nitrogen:oxygen)	0	<u>L9</u>
<u>L8</u>	n2:o2	2	<u>L8</u>
<u>L7</u>	L4 and (high adj K) and oxidation and chamber	3	<u>L7</u>
<u>L6</u>	L5 and (silicon adj oxide)	9	<u>L6</u>
<u>L5</u>	L4 and (oxygen adj containing)	19	<u>L5</u>
<u>L4</u>	L2 and nitrogen and oxygen and (inert or hydrogen or argon or h2 or ar or xenon or xe or krypton or kr or neon or ne)	88	<u>L4</u>
<u>L3</u>	L2 and ((nitrogen and oxygen) near2 (ratio))	3	<u>L3</u>
<u>L2</u>	(semiconductor or wafer) and (micro) and (flow near ratio)	231	<u>L2</u>
<u>L1</u>	microstructure near5 (flow ratio)	2	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 7 of 7 returned.

1. Document ID: US 6620670 B2

L23: Entry 1 of 7

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of Al<sub>2</sub>O<sub>3</sub>

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KIND	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	------	---------

2. Document ID: US 6583463 B1

L23: Entry 2 of 7

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized Ta<sub>2</sub>O<sub>5</sub> capacitor insulator

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KIND	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	------	---------

3. Document ID: US 6548343 B1

L23: Entry 3 of 7

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KIND	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	------	---------

4. Document ID: US 6544875 B1

L23: Entry 4 of 7

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875  
DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)

5. Document ID: US 6485988 B2

L23: Entry 5 of 7

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988  
DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)

6. Document ID: US 6413386 B1

L23: Entry 6 of 7

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386  
DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)

7. Document ID: US 6362093 B1

L23: Entry 7 of 7

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093  
DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)

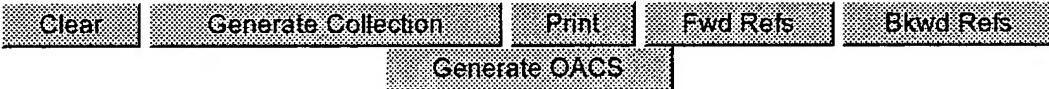
[Clear](#) | [Generate Collection](#) | [Print](#) | [Fwd Refs](#) | [Bkwd Refs](#) | [Generate OACS](#)

Terms	Documents
L22 and (silicon adj oxide)	7

Display Format:

[Previous Page](#)      [Next Page](#)      [Go to Doc#](#)

## Hit List



### Search Results - Record(s) 1 through 10 of 11 returned.

#### 1. Document ID: US 6659111 B1

L22: Entry 1 of 11

File: USPT

Dec 9, 2003

US-PAT-NO: 6659111

DOCUMENT-IDENTIFIER: US 6659111 B1

TITLE: Cleaning gas and method for cleaning vacuum treatment apparatus by flowing the cleaning gas



#### 2. Document ID: US 6620670 B2

L22: Entry 2 of 11

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of Al<sub>2</sub>O<sub>3</sub>

#### 3. Document ID: US 6583463 B1

L22: Entry 3 of 11

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized Ta<sub>2</sub>O<sub>5</sub> capacitor insulator

#### 4. Document ID: US 6548343 B1

L22: Entry 4 of 11

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KIN/C](#) | [Drawn D](#)

---

5. Document ID: US 6544875 B1

L22: Entry 5 of 11

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KIN/C](#) | [Drawn D](#)

---

6. Document ID: US 6509511 B1

L22: Entry 6 of 11

File: USPT

Jan 21, 2003

US-PAT-NO: 6509511

DOCUMENT-IDENTIFIER: US 6509511 B1

TITLE: Process for the conversion of perfluoroalkanes, a catalyst for use therein and a method for its preparation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KIN/C](#) | [Drawn D](#)

---

7. Document ID: US 6485988 B2

L22: Entry 7 of 11

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KIN/C](#) | [Drawn D](#)

---

8. Document ID: US 6413386 B1

L22: Entry 8 of 11

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Fight	Review	Classification	Date	Reference			Claims	KMC	Draw D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	-----	--------

**D 9. Document ID: US 6362093 B1**

L22: Entry 9 of 11

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

Full	Title	Citation	Fight	Review	Classification	Date	Reference			Claims	KMC	Draw D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	-----	--------

**D 10. Document ID: US 6238582 B1**

L22: Entry 10 of 11

File: USPT

May 29, 2001

US-PAT-NO: 6238582

DOCUMENT-IDENTIFIER: US 6238582 B1

TITLE: Reactive ion beam etching method and a thin film head fabricated using the method

Full	Title	Citation	Fight	Review	Classification	Date	Reference			Claims	KMC	Draw D
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	-----	--------

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate GACS
-------	---------------------	-------	----------	-----------	---------------

Terms	Documents
L21 and oxide and (oxygen adj containing)	11

Display Format: TI  Change Format[Previous Page](#)[Next Page](#)[Go to Doc#](#)

## Hit List

---

<a href="#">Clear</a>	<a href="#">Generate Collection</a>	<a href="#">Print</a>	<a href="#">Fwd Refs</a>	<a href="#">Bkwd Refs</a>
<a href="#">Generate OACS</a>				

---

### Search Results - Record(s) 11 through 11 of 11 returned.

---

11. Document ID: US 6218300 B1

L22: Entry 11 of 11

File: USPT

Apr 17, 2001

US-PAT-NO: 6218300

DOCUMENT-IDENTIFIER: US 6218300 B1

TITLE: Method and apparatus for forming a titanium doped tantalum pentaoxide dielectric layer using CVD

---

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Text](#) | [Image](#) | [Claims](#) | [KIMC](#) | [Draw](#) | [D](#)

---

---

<a href="#">Clear</a>	<a href="#">Generate Collection</a>	<a href="#">Print</a>	<a href="#">Fwd Refs</a>	<a href="#">Bkwd Refs</a>	<a href="#">Generate OACS</a>
-----------------------	-------------------------------------	-----------------------	--------------------------	---------------------------	-------------------------------

---

Terms	Documents
L21 and oxide and (oxygen adj containing)	11

---

Display Format:  [Change Format](#)

[Previous Page](#)    [Next Page](#)    [Go to Doc#](#)

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

### Search Results - Record(s) 1 through 3 of 3 returned.

#### □ 1. Document ID: US 6387819 B1

L3: Entry 1 of 3

File: USPT

May 14, 2002

US-PAT-NO: 6387819

DOCUMENT-IDENTIFIER: US 6387819 B1

TITLE: Method for etching low K dielectric layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMPC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

#### □ 2. Document ID: US 6110609 A

L3: Entry 2 of 3

File: USPT

Aug 29, 2000

US-PAT-NO: 6110609

DOCUMENT-IDENTIFIER: US 6110609 A

TITLE: Magnetic thin film and magnetic head using the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMPC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

#### □ 3. Document ID: US 4543707 A

L3: Entry 3 of 3

File: USPT

Oct 1, 1985

US-PAT-NO: 4543707

DOCUMENT-IDENTIFIER: US 4543707 A

TITLE: Method of forming through holes by differential etching of stacked silicon oxynitride layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMPC	Drawn D
------	-------	----------	-------	--------	----------------	------	-----------	--------	------	---------

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
-------	---------------------	-------	----------	-----------	---------------

Terms	Documents
L2 and ((nitrogen and oxygen) near2 (ratio))	3

Display Format:  [Change Format](#)

[Previous Page](#)    [Next Page](#)    [Go to Doc#](#)